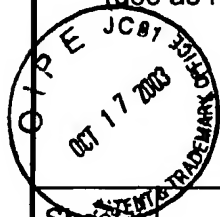


PTO/SB/08A			<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)			Application Number	10/615,127
			Filing Date	July 24, 2003
			Confirmation Number	8157
			First Named Inventor	Falster et al
			Group Art Unit	1765
			Examiner Name	H. Jeshen
			Attorney Docket No.	MEMC TP-01-2450 (3009)
Sheet	1	of	4	



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Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code <sup>2</sup> (if known)		
F.H. /	1	4,314,595		Yamamoto et al	02/09/1982
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	3	4,437,922		Bischoff et al	03/20/1984
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F.H.	16	5,674,756		Sato et al	10/07/1997
Examiner Signature	H. Jeshen		Date Considered	1/4/04	

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		Group Art Unit	1745
		Examiner Name	Hiteshew
Sheet 2 of 4	Attorney Docket No.	MEMC TP-01-2450 (3009)	

F.H.	17	5,738,942		Kubota et al	04/14/1998
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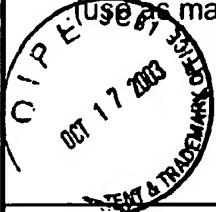
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		Office	Number <sup>4</sup>	Kind Code <sup>2</sup> (if known)			
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↓	30	JP	5155700		Atsushi et al	06/22/1993	A
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		Examiner Name	Hiteshen		
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F <sub>2</sub> H <sub>1</sub>	32	JP	7321120		Shiro et al	12/08/1995	A
↑	33	JP	7335657		Masahiko	12/12/1995	A
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### OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
F <sub>2</sub> H <sub>1</sub>	41	FALSTER, R., et al, The Engineering of Silicon Wafer Material Properties Through Vacancy Concentration Profile Control and the Achievement of Ideal Oxygen Precipitation Behavior, Mat. Res. Soc. Symp. Proc., vol. 510, 1998, p. 27-35	
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Examiner Signature	<i>J. Hiteshen</i>	Date Considered	1/4/04
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		Group Art Unit	1765		
		Examiner Name	H. Yeshaw		
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FA	45	JACOB, M., et al, Influence of TRP on Vacancy Concentrations, Mat. REs. Soc. Symp. Proc., Vol. 490, 1998, p. 129-134	
↑	46	NADAHARA, S., et al, Hydrogen Annealed Silicon Wafer, Solid State Phenomena, Vols. 57-58, 1997, p. 19-26	
↓	47	PAGANI, M., et al, Spatial Variations in Oxygen Precipitation in Silicon After High Temperature Rapid Thermal Annealing, Appl. Phys. Lett., Vol. 70, No. 12, 1997, p. 1572-1574	
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FA	50	SHIMURA, F., Semiconductor Silicon Crystal Technology, Academic Press, Inc., San Diego, CA, 1989, p. 361-377	

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